Amendments to the Claims:

This listing of claims will replace all prior versions and listings of claims in the application:

Listing of Claims:

1 (original): A method for manufacturing a ternary nitride-based buffer layer of a nitride-based light-emitting device, comprising the steps of:

providing a substrate;

introducing a first reaction source comprising a first group III element into a chamber at a first temperature, the melting point of the first group III element being lower than the first temperature, wherein the first group III element is deposited on the substrate; and

introducing a second reaction source comprising a second group III element and a third reaction source comprising a nitrogen element into the chamber at a second temperature for forming a ternary nitride-based buffer layer with the first group III element on the substrate, wherein the second temperature is not lower than the melting point of the first group III element.

2 (original): The method of claim 1, wherein the substrate comprises at least a material selected from the group consisting of sapphire, GaN, AlN, SiC, GaAs, GaP, Si, ZnO, MgO, MgAl2O4, glass, and the like.

3 (original): The method of claim 1, wherein the first temperature is 500℃ or above.

4 (original): The method of claim 1, wherein the second temperature is 700℃ or above.

5 (original): The method of claim 1, wherein the first group III element comprises at least a material selected from the group consisting of Al, Ga, In, and the like.

6 (original): The method of claim 1, wherein the second group III element comprises at least a material selected from the group consisting of Al, Ga, In, and the like.

7 (original): The method of claim 1, wherein the ternary nitride-based buffer layer thickness is between 1nm and 500nm.

8 (original): The method of claim 1, wherein the ternary nitride-based buffer layer comprises at least a material selected from the group consisting of InGaN, AlGaN, InAlN, and the like.

9-19 (cancelled).